



7, Autogennaya Str., Kharkov, 61099, Ukraine. Phone: (+38-057) 728-1244, 728-1241. Fax: (+38-057) 728-1243, (+38-0572) 946-830 E-mail: market@yuzhcable.com.ua

# АПвЭСПу-30 1х185 ТУ У 27.3-00214534-092:2016



Single-core power cables with aluminium conductors, XLPE-insulated, with copper screen, lead-sheathed, with reinforced outer sheath of polyethylene

Technical cable requirements correspond to IEC 60502-2

Cables are used for laying:

- in places, where small mechanical impacts on cable are possible, including tensile forces
- in soil (trenches) with high corrosiveness
- in damp, partially flooded premises
- in wetlands
- in non-navigable waters
- on difficult route sections, according to the unique specification
- in the air, including cable structures, if provided the additional fire protection

It is possible to manufacture cables with extruded semiconductor layer along outer sheath. Order entry example:

АПвЭСПу-П-30 1х185/25 ТУ У 27.3-00214534-092:2016

An extruded semiconductor layer along outer sheath ensures the correct testing of cable line with sections of underground laying in polymer pipes.

It is possible to manufacture cables with an integrated fiber-optic module.

Order entry example:

АПвЭСПу-30 1х185/25 (ОМ) ТУ У 27.3-00214534-092:2016

In conjunction with the DTS system, the integrated fiber-optic module can act as a distributed cable line temperature sensor.

Cables without copper screen can also be manufactured

It is possible to manufacture cable with Order entry example: АПвЭСПу-30 1x185/25 (ожк) ТУ У 27.3-00214534-092:2016

It is possible to manufacture cable with sealed conductor. Order entry example: ΑΠβΘCΠy-30 1x185/25 (г) ΤУ У 27.3-00214534-092:2016





7, Autogennaya Str., Kharkov, 61099, Ukraine. Phone: (+38-057) 728-1244, 728-1241. Fax: (+38-057) 728-1243, (+38-0572) 946-830 E-mail: market@yuzhcable.com.ua

# АПвЭСПу-30 1x185 ТУ У 27.3-00214534-092:2016

Single-core power cables with aluminium conductors, XLPE-insulated, with copper screen, lead-sheathed, with reinforced outer sheath of polyethylene

## **TECHNICAL SPECIFICATIONS**

30 36 1 x 185 8 2 10.10 17.5 424 504 317 324 6
1 x 185 8 2 10.10 17.5 424 504 317 324
8 2 10.10 17.5 424 504 317 324
2 10.10 17.5 424 504 317 324
10.10 17.5 424 504 317 324
17.5 424 504 317 324
424 504 317 324
504 317 324
504 317 324
317 324
324
6
0
+90
+130
+250
-60 +50
1225
49
5210
# 22УД-60: 661 • 4.4
# 20аУД-60: 810 • 4.9
-

Notes:

When ordering it is neccesary to agree the factory length of the product with the manufacturer

\* Long permissible current loads are calculated for the following conditions: conductor temperature 90 °C, air temperature 30 °C, soil temperature 20 °C, thermal resistivity of soil 1.5 °K • m/W, laying depth in the soil 0.8 m, while laying in flat formation the distance between cables in clear is equal to the cable diameter, while laying in trefoil formation cables are laid side by side, shields are earthed on both ends of the line

 $^{**}$  The external diameter may differ from the rated up to  $\pm$  10 %



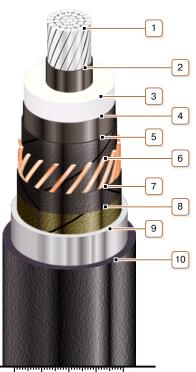


7, Autogennaya Str., Kharkov, 61099, Ukraine. Phone: (+38-057) 728-1244, 728-1241. Fax: (+38-057) 728-1243, (+38-0572) 946-830 E-mail: market@yuzhcable.com.ua

# АПвЭСПу-30 1х185 ТУ У 27.3-00214534-092:2016



Single-core power cables with aluminium conductors, XLPE-insulated, with copper screen, lead-sheathed, with reinforced outer sheath of polyethylene



### 0 10 20 30 40

## CONSTRUCTION

- 1. Aluminium multiwire compacted conductor
- Notes: • It is possible to manufacture cable with a single-wire conductor • It is possible to manufacture cable with sealed conductor.
- 2. Inner extruded semiconducting layer
- 3. XLPE insulation
- 4. Outer extruded semiconducting layer
- Lapping layer of semiconductive swellable tape
  Copper screen
- Note: Cables without copper screen can also be manufactured
- 7. Lapping layer of semiconductive swellable tape
- 8. Lapping layer of semiconductive tape
- 9. Lead sheath

### 10. Strengthened polyethylene outer sheath

Note: It is possible to manufacture cable with extruded semiconductor layer along outer sheath